

Triple 3-Input NOR Gate in bare die form

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Description

The 74HC27 triple 3-Input NOR Gate is fabricated on a 2.5µm 5V CMOS process combining high speed LSTTL performance with CMOS low power. The device contains three independent 3-input NOR gates performing Boolean function Y = $(\overline{A} + \overline{B} + \overline{C})$ or Y = $\overline{A} \cdot \overline{B} \cdot \overline{C}$ in positive logic. Internal circuitry comprises of three stages and includes buffered output for high noise immunity and stability. Inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

Features:

- Output Drive Capability: 10 LSTTL Lyads
- Low Input Current: 1µA
- Outputs directly interface CNCS NMOS and TTL
- Operating Voltage Range: 2% to 6V
- Function compatible with 54LS27
- High Noise Immunity CMOS process.

Ordering Information

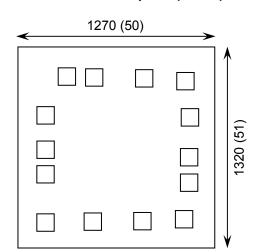
The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product please see

54HC27

Die Dipiensions in µm (mils)



Supply Formats:

- Defaut Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Mechanical Specification

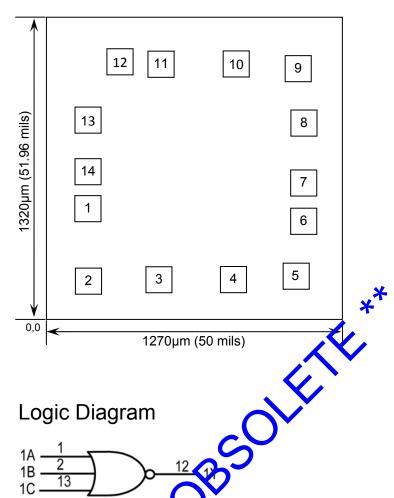
Die Size (Unsawn)	1270 x 1320 50 x 51	µm mils	
Minimum Bond Pad Size	108 x 108 4.25 x 4.25	μm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	μm mils	
Top Metal Composition	Al 1%Si 1.1μ	m	
Back Metal Composition	N/A – Bare Si		





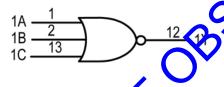
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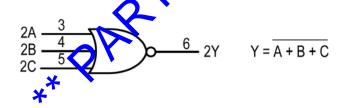
Pad Layout and Functions



PAD	FUNCTION	COORDINA	ATES (mm)
FAD	TONCTION	Х	ν Υ
1	1A	0.123	0.442
2	1B	ે 132	0.124
3	2A	0.433	0.133
4	2Б	0.751	0.133
5	2C	1.017	0.148
6	21	1.047	0.392
7	GND	1.047	0.561
δ	3 Y	1.047	0.828
9	3A	1.017	1.073
10	3B	0.751	1.088
11	3C	0.433	1.088
12	1Y	0.262	1.095
13	1C	0.128	0.838
14	V _{CC}	0.129	0.606
CON	NECT CHIP BA	CK TO V _{CC} O	R FLOAT

Logic Diagram





Pad 14 = V_{CC} Pad 7 = GND

Truth Table

	NPUTS	OUTPUT	
Α	В	С	Υ
Н	Χ	X	L
X	Н	X	L
X	X	H	L
L	L	L	H

H = High level (steady state) L = Low level (steady state) X = don't care



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Absolute Maximum Ratings¹

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V _{CC}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V _{IN}	-1.5 to V _{CC} +1.5	V
DC Output Voltage (Referenced to GND)	V _{OUT}	-0.5 to V _{CC} +0.5	
DC Input Current	I _{IN}	±20	mA
DC Output Current, per pad	I _{OUT}	±25	mA
DC Supply Current, V _{CC} or GND	I _{CC}	±50	mA
Power Dissipation in Still Air ²	P _D	750	mW
Storage Temperature Range	T _{STG}	-65 (0 150	°C

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die alach and assembly method.

Recommended Operating Conditions³ (Voltages reverenced to GND)

	•		_	
PARAMETER	SYMBOL	MIN 🧪	MAX	UNITS
Supply Voltage	V _{CC}	2	6	V
DC Input or Output Voltage	V _{IN} ,V _{OUT}	0	V _{CC}	V
Operating Temperature Range	TJ	-40	+85	°C
	V _{CC} = 2V	0	1000	
Input Rise or Fall Times	t _r , t _f V 4.5V	0	500	ns
	V _{CC} ¥ 6.0V	0	400	

^{3.} This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range $GND \le (V_{IN} \text{ or } V_{OUT}) \le V_{C}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC Electrical characteristics (Voltages Referenced to GND)

PARAMETER SYMBOL	SYMBOL	V _{cc}	CONDITIONS	LIMITS			UNITS
	• 66	VCC GONDINGNO	25°C	85°C	FULL RANGE⁴	Julio	
Minimum Ligh-Level Input Voltage		2.0V	V _{OUT} = 0.1V or	1.5	1.5	1.5	V
	V _{IH}	$ \begin{array}{ c c c c }\hline 4.5V & V_{CC} - 0.1V \\\hline 6.0V & I_{OUT} \le 20 \mu A \\\hline \end{array} $		3.15	3.15	3.15	
			I _{OUT} ≤ 20μA	4.2	4.2	4.2	
Maximum Low-Level Input Voltage		2.0V	V _{OUT} = 0.1V or	0.3	0.3	0.3	
	V _{IL}	4.5V	V _{CC} -0.1V	0.9	0.9	0.9	V
		6.0V	I _{OUT} ≤ 20μA	1.2	1.2	1.2	

^{4.} -40°C ≤ T_J ≤ +85°C





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DC Electrical Characteristics Continued (Voltages Referenced to GND)

PARAMETER	SYMBOL	V _{cc}	CONDITIONS		LIM	ITS	UNITS
TANAMETER	OTHIDOL	₩00	CONDITIONS	25°C	85°C	FULL RANGE⁴	
		2.0V	\/ =\/ or\/	1.9	1.9	1.9	
		4.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 20 \mu A$	4.4	4.4	4.4	
Minimum High-Level		6.0V	1 0011 -1	5.9	5.9	5.9	V
Output Voltage	V _{OH}	4.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 4.0 \text{mA}$	3.98	3.84	3.64	V
		6.0V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 5.2 \text{mA}$	5.48	5.34	5.34	
		2.0V	$V_{IN} = V_{IL} \text{ or } V_{IL}$ $ I_{OUT} \le 20\mu\text{A}$	0.1	01	0.1	
		4.5V		0.1	0.1	0.1	
Maximum Low-Level		6.0V	1 0011 -1	0.1	9.1	0.1	
Output Voltage	V _{OL}	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 4.0 \text{mA}$	2.26	0.33	0.33	V
		6.0V	$V_{IN} = V_{IL} \text{ or } V_{IL}$ $\left I_{OUT} \right \le 5.2 \text{mA}$	0.26	0.33	0.33	
Maximum Input Leakage Current	I _{IN}	6.0V	V _{IN} = V _{CC} or SND	±0.1	±1.0	±1.0	μA
Maximum Quiescent Supply Leakage Current	Icc	6.0V	V _{IN} = V _N or GND I _{O IT} = υμΑ	2	20	20	μА

AC Electrical Characteristics⁵

PARAMETER	PARAMETER SYNBOL Vcc	Voc	/cc CONDITIONS	LIMITS			UNITS
ANAMETER		• 66		25°C	85°C	FULL RANGE⁴	00
Maximum Propagation	t _{PLH} , t _{PHL}	2.0V 4.5V 6.0V		90	115	115	
Delay, Input A, 3 o C			$C_L = 50pF,$ $t_r = t_f = 6ns$	18	23	23	ns
to Output Y (Figure 2)			t _r - t _f - 0115	15	20	20	
Maximum Output Rise		2.0V 4.5V		75	95	95	
and Fall Time, Any Output	t _{TLH,} t _{THL}		$C_L = 50pF,$ $t_r = t_f = 6ns$	15	19	19	ns
(Figure 1,2)		6.0V	t _r - t _f - 0115	13	16	16	

^{5.} Not production tested in die form, characterized by chip design and tested in package.





AC Electrical Characteristics Continued⁵

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PARAMETER	SYMBOL	V _{cc}	CONDITIONS		LIM	ITS	UNITS
	OTHEOL	• 66	CONDITIONS	25°C	85°C	FULL RANGE⁴	
Maximum Input Capacitance	C _{IN}	-	-	10	10	10	pF
Power Dissipation Capacitance Per Gate ⁶	C _{PD}	-	$T_J = 25^{\circ}C,$ $V_{CC} = 5.0V$		TYPI 2		pF

^{6.} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

Switching Waveform

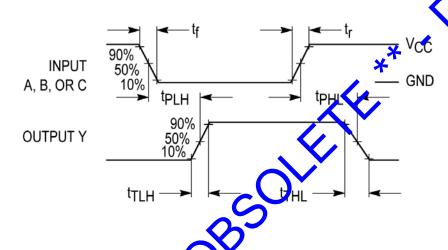
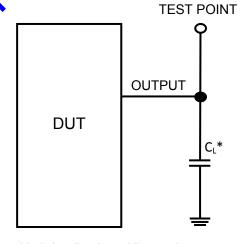


Figure 1 - Propagation Delay & Output Transition Time

Test Circuit



^{*} Includes all probe and jig capacitance

Figure 2

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